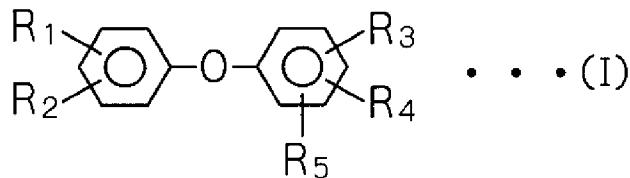


AMENDMENTS TO THE CLAIMS

1. **(Currently amended)** A developer composition for positive resists, comprising 2 to 5% by mass of tetramethylammonium hydroxide and a surfactant in an aqueous solution, said surfactant containing an anionic surfactant represented by the following general formula (I):



wherein at least one member of R₁ and R₂ represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any remaining member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of R₃, R₄ and R₅ represents a group represented by the following general formula (II):



wherein M represents a metal atom selected from the group consisting of sodium, potassium, and calcium, and any remaining member represent a hydrogen atom or a group represented by the above general formula (II), provided that, in the general formula (I), when two or more groups represented by the general formula (II) are present, M may be the same or different, wherein

the amount of said anionic surfactant is in the range of 1,000 to 50,000 ppm based on said developer composition, and wherein said positive resists comprising comprise a novolak resin and a naphthoquinone diazide compound.

2. **(Cancelled)**

3. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer,

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selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern

4. **(Canceled)**